

## Schottky Barrier Diode

VOLTAGE RANGE: 30V PEAK PULSE POWER:200mW

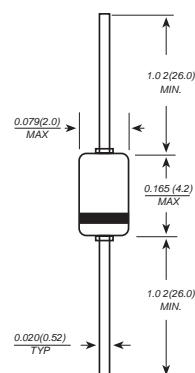
### Features

- VR 30V
- IFM 300mA
- Applications where a very low forward voltage is required

### MECHANICAL DATA

- Case: DO-35
- Polarity: Color band denotes cathode end
- Mounting Position: Any

DO-35(GLASS)



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

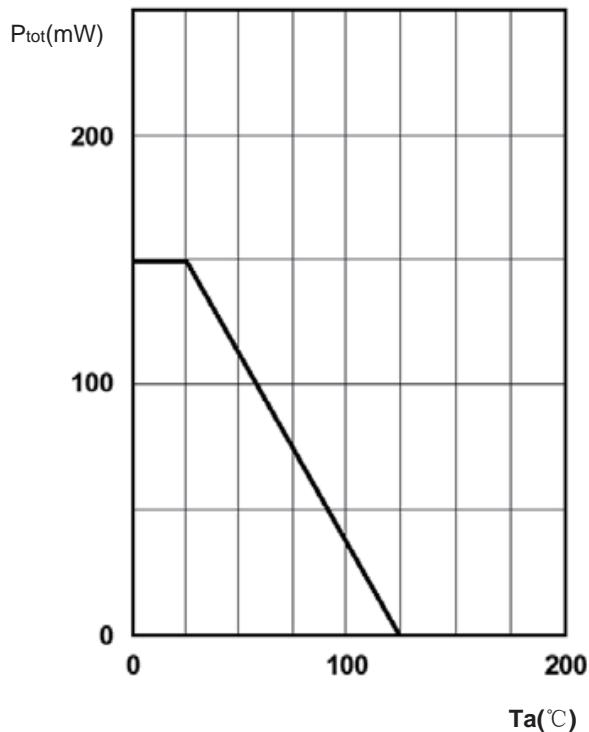
Item	Symbol	Unit	Conditions	Max
Continuous reverse voltage	V <sub>R</sub>	V		30
Forward continuous current	I <sub>F</sub>	mA	T <sub>a</sub> =25°C	200
Peak forward current	I <sub>FM</sub>	mA	T <sub>a</sub> =25°C	300
Surge forward current	I <sub>FSM</sub>	mA	t <sub>p</sub> ≤1s, T <sub>a</sub> =25°C	600
Power dissipation	P <sub>tot</sub>	mW	T <sub>a</sub> =65°C	200
Maximum junction temperature	T <sub>j</sub>	°C		125
Ambient operating temperature range	T <sub>A</sub>			-65 to +125
Storage temperature range	T <sub>stg</sub>	°C		-65 to +150
Junction ambient	R <sub>thJA</sub>	°C/W	On PC board 50mm×50mm×1.6mm	250

### Electrical Specification (T<sub>A</sub>=25°C unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Max
Reverse breakdown voltage	V <sub>(BR)R</sub>	V	I <sub>R</sub> =10uA (pulsed)	30	
Leakage current	I <sub>R</sub>	uA	V <sub>R</sub> =25V		2
Forward voltage pulse test tp<300us,s<2%	VF	V	I <sub>F</sub> =0.1mA		0.24
		V	I <sub>F</sub> =1mA		0.32
		V	I <sub>F</sub> =10mA		0.4
		V	I <sub>F</sub> =30mA		0.5
		V	I <sub>F</sub> =100mA		0.8
Capacitance	C <sub>tot</sub>	pF	V <sub>R</sub> =1V, f=1MHz		10
Reverse recovery time	t <sub>rr</sub>	ns	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>R</sub> =0.1mA		5

## RATINGS AND CHARACTERISTIC CURVES

Fig1. Admissible power dissipation vs. ambient temperature



characteristics

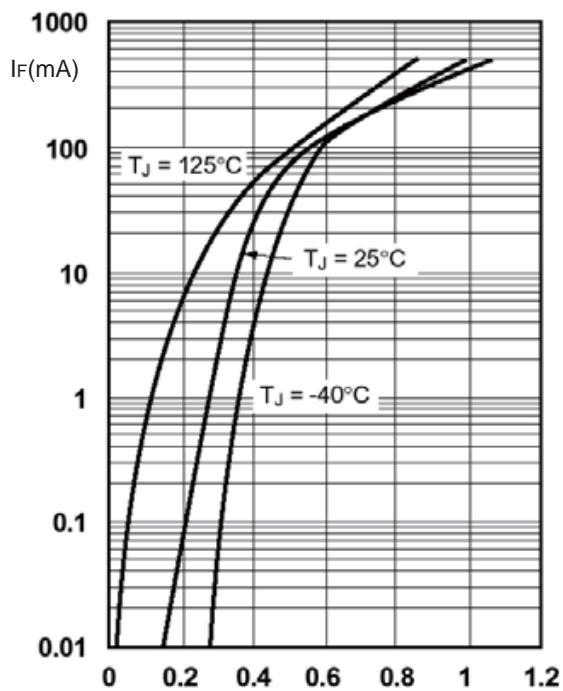


Fig3. Typical reverse characteristics

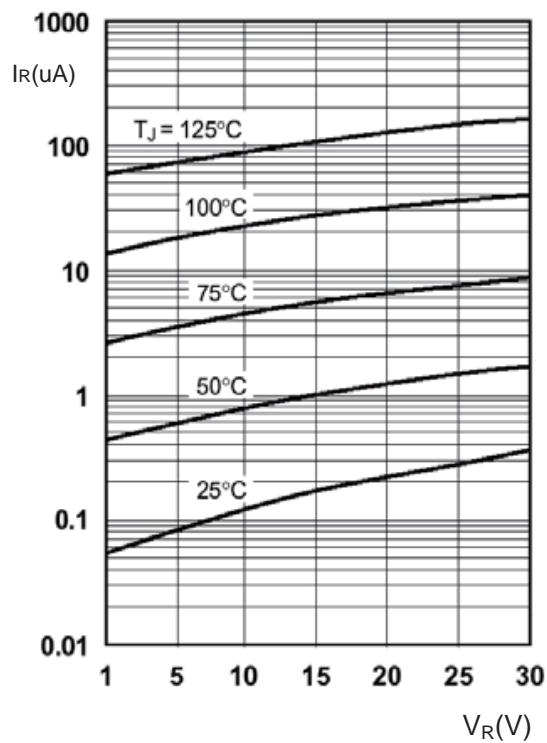


Fig4. Typical junction capacitance

